

[*ELECTROSTATIC DISCHARGE PROTECTION CIRCUIT*]

Abstract of Disclosure

The invention provides an ESD protection circuit compatible with the high voltage device manufacturing processes by using parasitic bipolar junction transistor punch characteristics. The design of the present invention takes advantage of bipolar punch characteristics of the parasitic NPN or PNP bipolar structure to bypass the ESD current, thus significantly increasing the ESD level. In addition, the ESD protection circuit of the present invention can greatly reduce the ESD cell areas by eliminating certain prior art diode structure.

